

# **PN4122**



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### **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA. Sourced from Process 66. See 2N3906 for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous		mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Max	Units	
		PN4122		
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

## PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS		1		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	40		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \ \mu A, I_C = 0$	5.0		V
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \mu \text{A}$	40		nA
I <sub>B</sub>	Base Cutoff Current	V <sub>CE</sub> = 30 V		25	nA
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30 V V <sub>CE</sub> = 30 V, T <sub>A</sub> = 65 °C		25 25	nA μA
	RACTERISTICS*	• • • •	•		
	DC Current Gain		100		
h <sub>FE</sub>		$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \mu\text{A}$ $V_{CE} = 1.0 V, I_{C} = 1.0 m\text{A}$	100 150		
		$V_{CE} = 1.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA}$	150	300	
		$V_{CE} = 1.0 \text{ V}, I_C = 50 \text{ mA}$	30	0.10	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$ $I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		0.13 0.14	V V
		$I_{\rm C} = 50$ mA, $I_{\rm B} = 5.0$ mA		0.30	v
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_{\rm C} = 1.0  {\rm mA}, I_{\rm B} = 0.1  {\rm mA}$		0.75	V
		$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$	0.70	0.90 1.10	V V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz		4.5	pF
C <sub>ib</sub>	Input Capacitance	V <sub>EB</sub> = 0.5 V, f = 1.0 MHz		8.0	pF
h <sub>fe</sub>	Small-Signal Current Gain	$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 20 V,	4.5		
		f = 100  MHz	150	450	
		$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1 kHz	150	400	
h <sub>ie</sub>	Input Impedance	$I_{\rm C} = 1.0  {\rm mA},  {\rm V}_{\rm CE} = 10  {\rm V},$	4.0	12	kΩ
h <sub>re</sub>	Voltage Feedback Ratio	f = 1.0 kHz		4.0	x10 <sup>-4</sup>
h <sub>oe</sub>	Output Admittance		8.0	40	μmhos
rb'Cc	Collector-Base Time Constant	$V_{CE} = 20 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$ f = 80 MHz		50	ps
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA},$			
		$R_{s} = 100 \Omega$ , f = 100 MHz,			
		$B_{w} = 15 \text{ MHz}$		6.0	dB
				4.0	dB
SWITCH	ING CHARACTERISTICS	$V_{cc} = 30 \text{ V}, \text{ I}_{c} = 50 \text{ mA},$		40	ns
tan	Delay Time	$I_{B1} = 5.0 \text{ mA}, V_{BE(off)} = 3.0 \text{ V}$		15	ns
		$_{B1} = 0.0 \text{ mm}, \text{ v}_{BE}(\text{ off}) = 0.0 \text{ v}$		40	ns
t <sub>d</sub>					
t <sub>d</sub>	Rise Time	$V_{12} = 30 V_{12} = 50 m^{4}$			
t <sub>d</sub> t <sub>r</sub> t <sub>off</sub>	Rise Time Turn-off Time	$V_{CC} = 30 \text{ V}, \text{ I}_{C} = 50 \text{ mA}$		150	ns
ton td tr toff ts tf	Rise Time	$V_{CC} = 30 \text{ V}, \text{ I}_{C} = 50 \text{ mA}$ $I_{B1} = I_{B2} = 5.0 \text{ mA}$			

\*Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

**PN4122** 



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